

**Listing of Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 1-65 without prejudice or disclaimer.

Please add the following new claims:

66. (New) A semiconductor device comprising:

a silicon semiconductor chip having an element formation surface and a back surface at an opposite side of the element formation surface;

an electrode formed on the element formation surface of the substrate and made of pure Al excluding an impurity;

a barrier metal disposed between the electrode and the substrate, for preventing silicon from being dissolved in the electrode; and

an emitter terminal, a collector terminal and a gate terminal, wherein the emitter terminal and the collector terminal are disposed to face the gate terminal.

67. (New) The semiconductor device of claim 66, wherein the silicon semiconductor chip is either a IGBT chip or a FWD chip.

68. (New) The semiconductor device of claim 66, further comprising a resin concavity portion disposed in a direction perpendicular to an extending direction of the emitter terminal, the collector terminal and the gate terminal.

.69. (New) The semiconductor device of claim 66, further comprising  
a land formed on the element formation surface of the substrate on the silicon  
semiconductor chip; and  
a metallic film disposed on the electrode and not disposed on the land.